1:

- 2

eformation potentials at I Zero of d bands above ; zation 32 eV Ed=5.75 th e

the relative change of the volume

of e2 at 4.05 eV, which ilarity of W11+2W12 a changes of M and J whi only do not contrib ore, Wij has its maximum t and where the contril total  $\epsilon_2$  is still small. would have the large a contribution of  $L_2' \rightarrow l$ s of M and J is justified analysis of the previothe effect of shear strain

 $+L_1$  selection rules and k = L is parallel t With spin, these rules w  $(|M_{z'}|^2 \ll |M_{z'}|^2)$ . The e different from the on n. The strong localizatio ssures that this deviation of the transition will b ations from the selection

is determined from e ng the assumption di  $\partial e = (-9.6 \pm 1.5) \text{ eV an}$ eV for k parallel [111] ese coefficients is due to the values given earlier ckground slope used wa used here).

## on Potentials at L

the deformation poter. s given earlier<sup>12</sup> neglecte the wave function of th tion. The treatment out idization.

uiltonian developed by workers,33 and Mueller

ce, edited by W. A. Harriscons, Inc., New York, 1960

Phys. Letters 10, 203 (1965 D. Lang, Phys. Rev. 15.

659 (1967).

## ELECTRONIC STRUCTURE OF Cu

TABLE VI. Deformation potentials (in eV) of the transitions at L. Experiment Theory Present Present formation paper DFJb Jacobs paper Zallenª mentials  $-72 \pm 12$ -56  $(-E_F)/\partial e_{yz}$  $(-E_F)/\partial e^d$  $-9.6\pm1.5$  $9.7 \pm 2.0$ 5.1  $-1.1\pm0.1$ Absolute -0.8Is-La")/de value <1.3 -5.9-4.1-L3")/de

• Reference 47. • Reference 43.

Reference 48.  $V = \lambda V/V$  is the relative change of the volume V.

the form given by Cohen and Mueller.35 Using symetrized plane waves as well as symmetrized tightding functions, we can write down the eigenvalues of : and of  $L_3^{u,l}$  immediately:

$$L_2' = k^2 - V_{111}, \tag{7}$$

$$L_{3}^{l,u} = E_d + \pi - \delta \pm \left[ (\pi - \delta)^2 + 4.5(-\sigma + \delta)^2 \right]^{1/2}.$$
 (8)

The vector k is that of the L point, V111 is a pseudostential form factor,  $E_d$  gives the position of the dand above  $\Gamma_1$ , and  $\sigma \equiv (dd\sigma)$ ,  $\pi \equiv (dd\pi)$ , and  $\delta \equiv (dd\delta)$ are the two-center tight-binding integrals defined by inter and Koster.36 The two L1 levels are obtained om the secular equation

$$\begin{vmatrix} H_{\Phi\Phi} - E & H_{\Phi d} \\ H_{d\Phi} & H_{dd} - E \end{vmatrix} = 0.$$
(9)

The function d is a tight-binding Bloch sum symetrized to  $L_1$  and  $\Phi$  is a plane wave symmetrized to , and orthogonalized to d,

$$\Phi = (\varphi - b_d d)/C$$
.

The abbreviations used in Eq. (10) are

$$\varphi = (2/V)^{1/2} \cos(\mathbf{k} \cdot \mathbf{r}),$$
 (11)

(10)

$$b_d = \langle \varphi | d \rangle,$$
  
$$C^2 = 1 - b_d^2.$$

The matrix elements of Eq. (9) are

$$H_{dd} = E_d - 4(\pi - \delta), \qquad (1)$$

$$H_{\phi d} = (H_{\varphi d} - b_d H_{dd})/C, \qquad (15)$$

$$H_{\phi\phi} = (k^2 + V_{111} + V_{\varphi\varphi}^{(2)} + b_d^2 H_{dd} - 2b_d H_{\varphi d})/C^2.$$
(16)

We calculated  $b_d$  and the tight-binding integrals using the atomic wave function and the atomic potential alculated by Hartree and Hartree<sup>37</sup> and parametrized



FIG. 13. The dependence of the shear strain deformation potential  $\partial L_1/\partial e_{yz}$  on the strain coefficient of the orthogonality integral  $b_d$  [part (a) of the figure] and on the strain coefficient of the hybridization  $H_{\varphi d}$  [part (b) of the figure]. The value  $\partial b_d / \partial e_{yz} = 0.73$  was calculated using atomic d functions.

by Fletcher and Wohlfahrth.<sup>38</sup> The numerical values are given in Table V. The tight binding integrals agree with those calculated by Fletcher and Wohlfahrth. The value of the orthogonalization integral  $b_d$  given by Mueller<sup>34</sup> is 16% lower than the one reported here.

A first-principles calculation of the quantities  $E_d$ ,  $H_{\omega d}$ , and  $\Delta V_{\omega \omega}^{(2)}$  is extremely difficult and will not be attempted here. Instead, we determine them from the eigenvalues of Fig. 9,13,14 using the calculated values of  $b_d$  and of the tight-binding integrals. In particular, the value of the hybridization integral  $H_{\varphi d}$  is evaluated from the difference between  $H_{dd}$  (the eigenvalue of  $L_1^d$ , neglecting hybridization) and  $L_1^d$ .  $E_d$  is calculated from  $L_3 - \Gamma_1$  using Eq. (8).  $(L_3^u - L_3^l$  given by this equation agrees with the value taken from Fig. 9. One would expect this, since these bands have no interaction with the sp bands.) The form factor  $V_{111}$  given by Eq. (7) is also taken from the calculated band structure.

 $\Delta V_{\varphi\varphi}^{(2)}$  is the matrix element of the crystal potential, (12)calculated with the l=2 component of  $\varphi$ . It was introduced in the model Hamiltonian<sup>35</sup> following a sugges-(13)tion by Heine.<sup>39</sup> Its numerical value (calculated using the  $L_1 - L_1^d$  gap of Fig. 9) is small, namely, -0.75 eV. Neglecting  $\Delta V_{\varphi\varphi}^{(2)}$  gives  $L_1 - L_1^d = 9.85$  eV using Eq. 4) (9), which is only 0.60 eV higher than the value of Fig. 9.  $\Delta V_{\varphi\varphi}^{(2)}$  will be neglected in the following. The zero-strain values of  $V_{111}$ ,  $H_{\varphi d}$ , and  $E_d$  are listed in Table V.

> The tight-binding parameters for changed nearestneighbor distances were calculated in the same way as for the distance in the unstrained crystal. For trigonal distortion (Table I) and levels with k parallel to [111], the strain coefficient of  $H_{dd}$  is (R is the nearest-neighbor

661

<sup>&</sup>lt;sup>11</sup> M. H. Cohen and F. M. Mueller, in *Atomic and Electronic iructure of Metals* (American Society for Metals, Metals Park, <sup>thio</sup>, 1967), p. 61.

<sup>&</sup>lt;sup>44</sup> J. C. Slater and G. F. Koster, Phys. Rev. 94, 1498 (1954). <sup>47</sup> D. R. Hartree and W. Hartree, Proc. Roy. Soc. (London) A157, 490 (1936).

<sup>&</sup>lt;sup>38</sup> G. C. Fletcher and E. P. Wohlfahrth, Phil. Mag. 42, 106 (1951)

<sup>39</sup> V. Heine, Phys. Rev. 153, 673 (1967).